

#### **Features**

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Positive Temperature Coefficient on V<sub>F</sub>

#### Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

# Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters



Part Number	Package	Qty(PCS)	
HIDW20G120C5B	TO247-3L	30	

### Maximum Ratings (Tc=25°C unless otherwise specified)

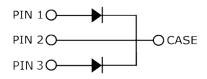
Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	v		
V <sub>RSM</sub>	Surge Peak Reverse Voltage	1300	V		
V <sub>DC</sub>	DC Blocking Voltage	1200	V		
I <sub>F</sub>	Continuous Forward Current (Per Leg/Device)	34/68 16.5/33 10/20	А	T <sub>c</sub> =25°C T <sub>c</sub> =135°C T <sub>c</sub> =157°C	Fig. 3
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	47* 31.5*	А	$T_c$ =25°C, $t_p$ =10 ms, Half Sine Pulse $T_c$ -110°C, $t_p$ =10 ms, Half Sine Pulse	
I <sub>FSM</sub>	Non-Repetitive Peak Forward Surge Current	71* 59.5*	А	$T_c=25^{\circ}C$ , $t_p=10$ ms, Half Sine Pulse $T_c=110^{\circ}C$ , $t_p=10$ ms, Half Sine Pulse	Fig. 8
$I_{F,Max}$	Non-Repetitive Peak Forward Current	750* 620*	А	$T_c=25^{\circ}C$ , $t_p=10$ ms, Pulse $T_c=110^{\circ}C$ , $t_p=10$ ms, Pulse	Fig. 8
P <sub>tot</sub>	Power Dissipation(Per Leg/Device)	176/352 76/152	w	T <sub>c</sub> =25°C T <sub>c</sub> =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V <sub>R</sub> =0-960V	
∫i²dt	i²t value	25* 17.5*	A²s	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms	
TJ	Operating Junction Range	-55 to +175	°C		
T <sub>stg</sub>	Storage Temperature Range	-55 to +135	°C		
	TO-247 Mounting Torque	1 8.8	Nm Ibf-in	M3 Screw 6-32 Screw	

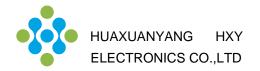


HIDW20G120C5B

Silicon Carbide Schottky Diode

TO247-3L Package





### **Electrical Characteristics (Per Leg)**

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
$V_{\rm F}$	Forward Voltage	1.5 2.2	1.8 3	V	I <sub>F</sub> = 10 A T <sub>J</sub> =25°C I <sub>F</sub> = 10 A T <sub>J</sub> =175°C	Fig. 1
I <sub>R</sub>	Reverse Current	30 55	250 350	μA	V <sub>R</sub> = 1200 V T <sub>J</sub> =25°C V <sub>R</sub> = 1200 V T <sub>J</sub> =175°C	Fig. 2
Q <sub>c</sub>	Total Capacitive Charge	52		nC	V <sub>R</sub> = 800 V, I <sub>F</sub> = 10A d <i>i</i> /d <i>t</i> = 200 A/µs T <sub>J</sub> = 25°C	Fig. 5
С	Total Capacitance	754 45 38		pF	$V_{R} = 0 V, T_{J} = 25^{\circ}C, f = 1 MHz$ $V_{R} = 400 V, T_{J} = 25^{\circ}C, f = 1 MHz$ $V_{R} = 800 V, T_{J} = 25^{\circ}C, f = 1 MHz$	Fig. 6
E <sub>c</sub>	Capacitance Stored Energy	14.5		μJ	V <sub>R</sub> = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

#### **Thermal Characteristics**

Symbol Parameter		Тур.	Unit	Note
R <sub>eJC</sub>	Thermal Resistance from Junction to Case	0.85 <sup>*</sup> 0.43 <sup>**</sup>	°C/W	Fig. 9

\* Per Leg, \*\* Per Device

# Typical Performance (Per Leg)

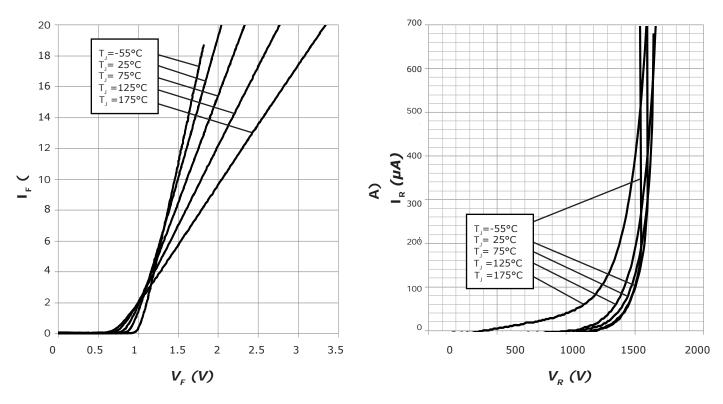


Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics



**Typical Performance (Per Leg)** 

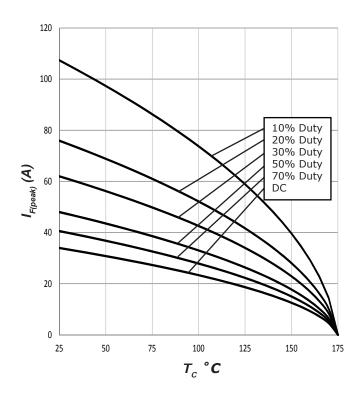
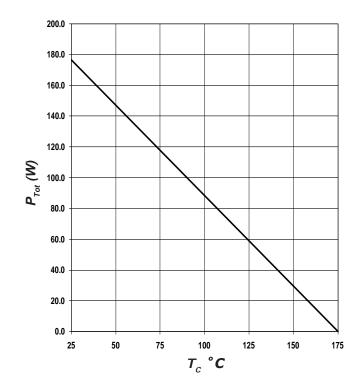


Figure 3. Current Derating





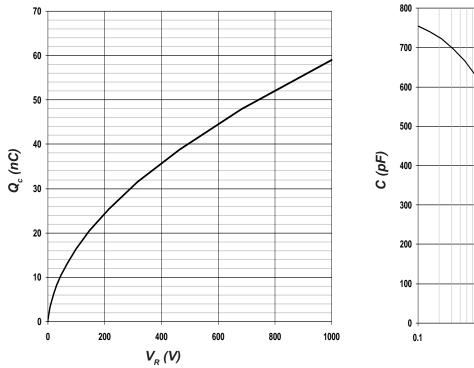


Figure 5. Recovery Charge vs. Reverse Voltage

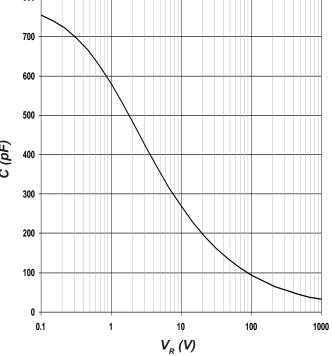
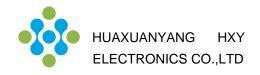


Figure 6. Capacitance vs. Reverse Voltage



**Typical Performance** 

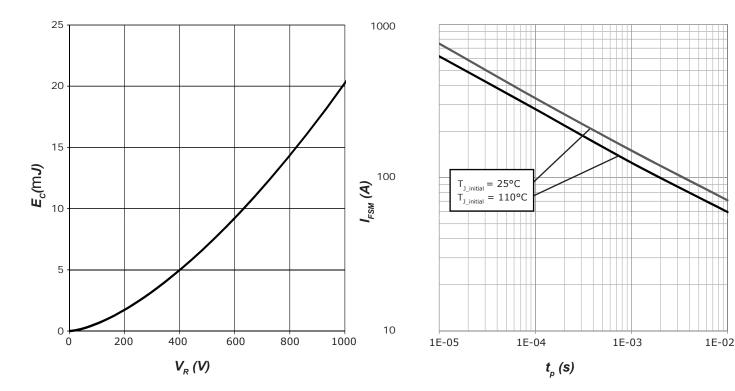


Figure 7. Typical Capacitance Stored Energy, per leg

Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform), per leg

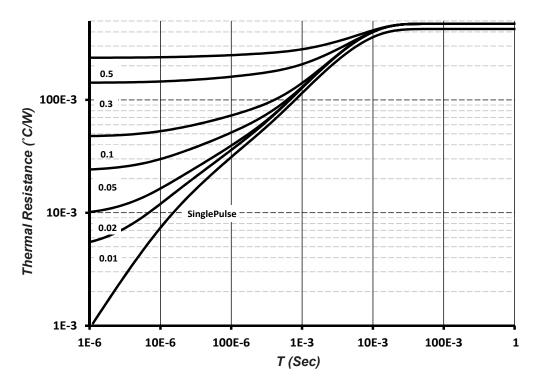
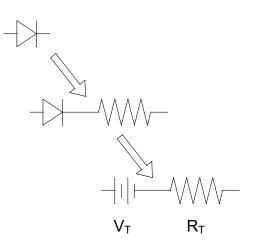


Figure 9. Device Transient Thermal Impedance



**Diode Model** 

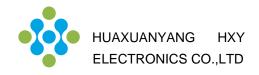


 $V_T$ +If\* $R_T$ 

$$V_{T} = 0.98 + (T_{J}^{*} - 1.71^{*}10^{-3})$$
  

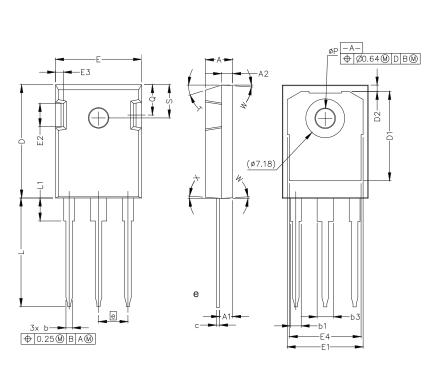
$$R_{T} = 0.040 + (T_{J}^{*} 5.32^{*}10^{-4})$$

Note:  $T_j$  = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

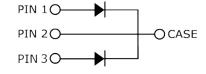


## Package Dimensions

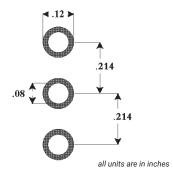
Package TO247-3L



POS	Inc	hes	Millimeters		
P03	Min	Max	Min	Мах	
А	.190	.205	4.83	5.21	
A1	.090	.100	.100 2.29		
A2	.075	.085	1.91	2.16	
b	.042	.052	1.07	1.33	
b1	.075	.095	1.91	2.41	
b3	.113	.133	2.87	3.38	
С	.022	.027	0.55	0.68	
D	.819	.831	20.80	21.10	
D1	.640	.695	16.25	17.65	
D2	.037	.049	0.95	1.25	
E	.620	.635	15.75	16.13	
E1	.516	.557	13.10	14.15	
E2	.145	.201	3.68	5.10	
E3	.039	.075	1.00	1.90	
E4	.487	.529	12.38	13.43	
е	.214	BSC	5.44 BSC		
L	.780	.800	19.81	20.32	
L1	.161	.173	4.10	4.40	
Ν	3				
ØP	.138	.144	3.51	3.65	
Q	.216	.236	5.49	6.00	
S	.238	.248	6.04	6.30	
Т	17.5° REF				
W	3.5° REF				
Х	4° REF				



# **Recommended Solder Pad Layout**





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